

AMENDMENTS TO THE SPECIFICATION:

Please replace paragraph [12] with the following amended paragraph:

[0012] Subsequently, ~~Under~~under the environment of 200~300°C, the protective film 10 is formed on the upper substrate 16 in use of E-beam deposition or sputtering methods, as shown in FIG.-33C.

Please replace paragraph [14] with the following amended paragraph:

[0014] However, after the protective film 10 is formed under the environment of 200~300 ~~200-300~~ °C, there occurs a crack in the area of the upper substrate 16 contacted with the sealing layer 50 due to the difference of thermal expansion coefficient between the upper substrate 16 and the sealing layer 50 in the course that it cools down to normal temperature. The difference of such thermal expansion coefficients generates partial thermal stress on a part where the upper substrate 16 is in contact with the sealing layer 50. There is generated a thermal stress which is relatively bigger in the upper substrate 16 than in the sealing layer 50, wherein the upper substrate 16 has relatively bigger thermal expansion coefficient than the sealing layer 50, and the thermal stress causes the crack to be generated in the upper substrate 16.